The JSM9435 uses advanced trench technology to provide excellent RDS(ON), shoot-through immunity, body diode characteristics and ultra-low gate resistance. This device is ideally suited for use as a low side switch in Notebook CPU core power conversion.

JSM9435采用先进的沟道技术，提供出色的无线电数据系统（ON）、穿透抗扰性、体二极管特性和超低栅极电阻。该设备非常适合用作笔记本电脑CPU核心功率转换的低端开关。

主要特性/Features

先进的沟槽工艺技术 Advanced trench process technology
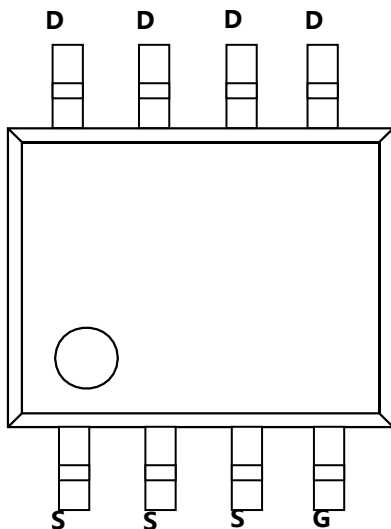高密度单元设计，超低导通电阻 High density cell design for ultra low on-resistance
高功率和电流处理能力 High power and current handing capability

应用/Application

蓄电池开关 Battery Switch
负荷开关   Load Switch

引脚定义/pin definition

电性能参数/Electrical Characteristics (TA=25℃unless otherwise noted)

Parameter	Description	Min.	Typ.	Max.	Test Conditions
V(BR)DSS	Drain-to-Source Breakdown Voltage	-30V			$V_{GS} = 0V$, $I_D = -250\mu A$
ID(Device Ref.)	Continuous Drain Current			-5.1A	$T_J = 25°C$
RDS(on)	Static Drain-to-Source On-Resistance		43mΩ	55mΩ	$V_{GS} = -10V$, $I_D = -5.1A$
RDS(on)	Static Drain-to-Source On-Resistance		62mΩ	90mΩ	$V_{GS} = -4.5V$, $I_D = -4.2A$
VGS(th)	Gate Threshold Voltage	-1.0V	-1.5V	-3.0V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$
IDSS	Drain-to-Source Leakage Current			1µA	$V_{DS} = -24V$, $V_{GS} = 0V$, $T_J = 25°C$
IGSS	Gate-to-Source Leakage Current			±100nA	$V_{GS} = ±20V$
T_j	Operating Junction and Storage Temperature Range	-55°C to 150°C Max.			
TSTG					

JSMICRO
SEMICONDUCTOR
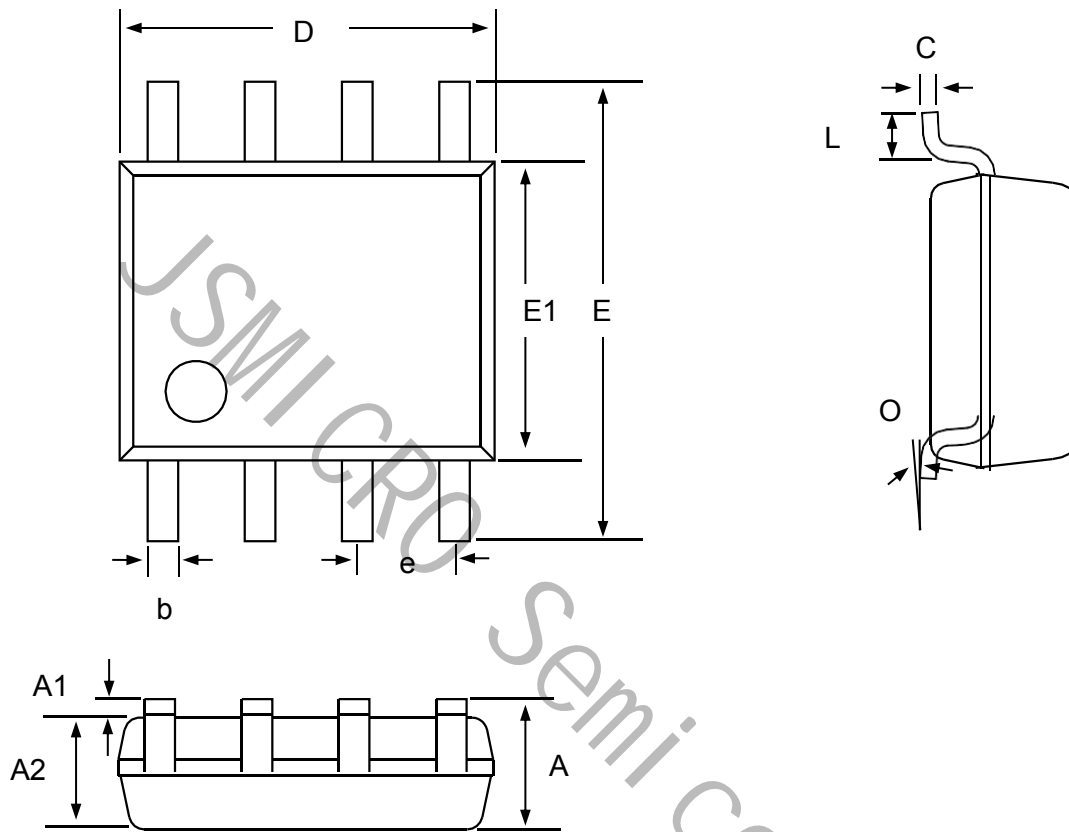
Symbol	Dim in mm		
	Min	Nor	Max
A	1.350	1.550	1.750
A1	0.100	0.175	0.250
A2	1.350	1.450	1.550
b	0.330	0.420	0.510
c	0.170	0.210	0.250
D	4.800	4.900	5.000
e	1.270(BSC)		
E	3.800	3.900	4.000
E1	0.400	0.835	1.2700
L	0°	4°	8°